

60 V, 2 A PNP/PNP low VCEsat (BISS) double transistor

15 December 2015

Product data sheet

1. General description

PNP/PNP low V_{CEsat} Breakthrough In Small Signal (BISS) double transistor in a leadless medium power DFN2020D-6 (SOT1118D) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

NPN/NPN complement: PBSS4260PANS

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability ${\rm I}_{\rm C}$ and ${\rm I}_{\rm CM}$
- High collector current gain h_{FE} at high I_C
- Reduced Printed-Circuit Board (PCB) requirements
- · Exposed heat sink for excellent thermal and electrical conductivity
- High energy efficiency due to less heat generation
- Suitable for Automatic Optical Inspection (AOI) of solder joints
- AEC-Q101 qualified

3. Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- LED lighting
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1.	Quick reference data
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per transistor	Per transistor						
V _{CEO}	collector-emitter voltage	open base		-	-	-60	V
I _C	collector current			-	-	-2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-3	А



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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per transistor							
R _{CEsat}	collector-emitter saturation resistance	$\begin{split} &I_C = -1 \text{ A}; I_B = -50 \text{ mA}; \text{ pulsed}; \\ &t_p \leq 300 \mu\text{s}; \delta \leq 0.02 ; T_{amb} = 25 ^\circ\text{C} \end{split}$		-	-	310	mΩ

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2	7 8	
4	E2	emitter TR2		
5	B2	base TR2	1 2 3	E1 B1 C2
6	C1	collector TR1	Transparent top view DFN2020D-6 (SOT1118D)	sym138
7	C1	collector TR1	DI 142020D-0 (SOTTIOD)	
8	C2	collector TR2		

6. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PBSS5260PAPS	DFN2020D-6	DFN2020D-6: plastic, thermally enhanced ultra thin and small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1118D		

7. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS5260PAPS	3Н

PBSS5260PAPS

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor		1			
V _{CBO}	collector-base voltage	open emitter		-	-60	V
V _{CEO}	collector-emitter voltage	open base		-	-60	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-3	А
I _B	base current			-	-0.3	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-1	А
P _{tot} total power	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	370	mW
			[2]	-	570	mW
			<u>[3]</u>	-	530	mW
			[4]	-	700	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	510	mW
			[2]	-	780	mW
			[3]	-	730	mW
			[4]	-	960	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

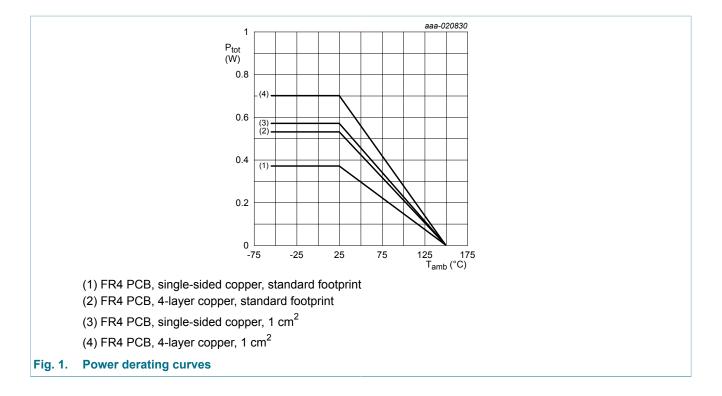
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single sided copper, tin-plated; mounting pad for collector 1 cm².

[3] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated and standard footprint.

[4] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated; mounting pad for collector 1 cm².

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9. Thermal characteristics

collector 1 cm².

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	338	K/W
from junction to ambient	-		[2]	-	-	219	K/W
	ampient		[3]	-	-	236	K/W
			[4]	-	-	179	K/W
Per device				1			
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	246	K/W
	from junction to ambient		[2]	-	-	161	K/W
	ampient		[3]	-	-	172	K/W
			[4]	-	-	131	K/W

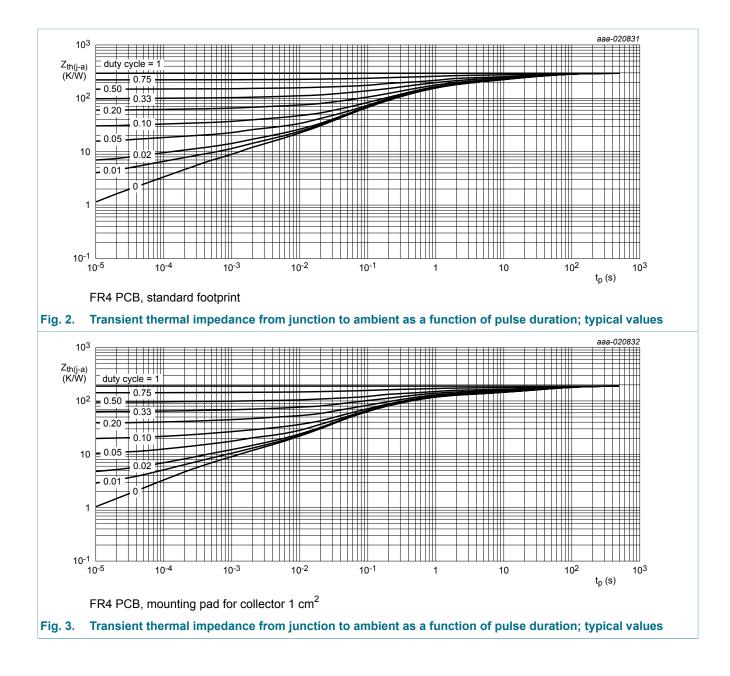
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated and standard footprint.
[4] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated, mounting pad for

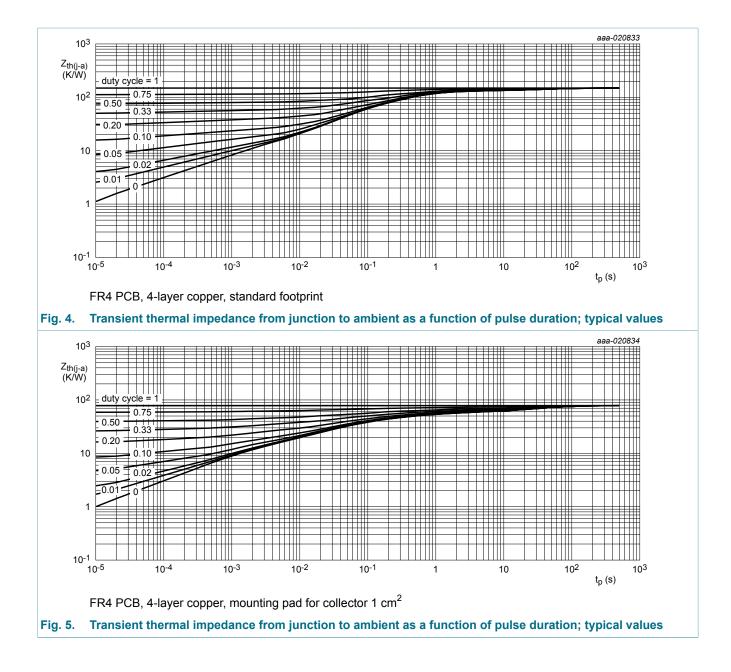
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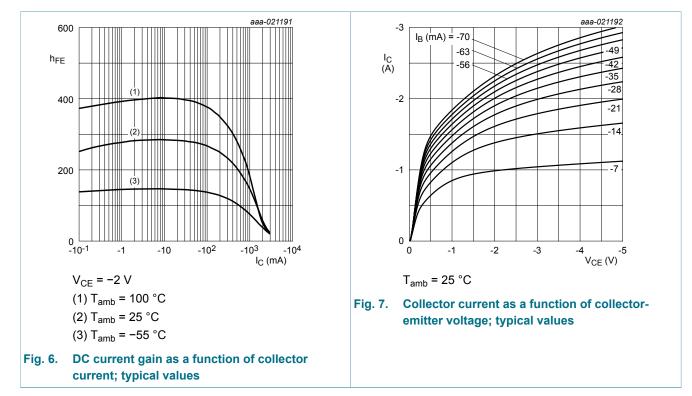
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor		I I			
I _{CBO} collector-base cut-off		V_{CB} = -48 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -48 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = -48 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	-100	nA
ЕВО	emitter-base cut-off current	V_{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I _C = -100 mA; pulsed; t _p ## 300 µs; $\delta \le 0.02$; T _{amb} = 25 °C	170	250	-	
		$\label{eq:VcE} \begin{array}{l} V_{CE} = -2 \ V; \ I_{C} = -500 \ mA; \ pulsed; \\ t_{p} \leq 300 \ \mus; \ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}C \end{array}$	140	200	-	
		$V_{CE} = -2 \text{ V; } I_C = -1 \text{ A; pulsed;}$ $t_p \le 300 \mu\text{s; } \delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	110	150	-	
		V_{CE} = -2 V; I _C = -2 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02	50	75	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -0.5 A; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-100	-140	mV
		$\begin{split} I_{C} &= -1 \text{ A}; I_{B} = -50 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \delta &\leq 0.02 ; T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-200	-310	mV
		$\begin{split} &I_C = -2 \text{ A}; \ I_B = -200 \text{ mA}; \text{ pulsed}; \\ &t_p \leq 300 \mu\text{s}; \ \delta \leq 0.02 \ \ ; \ T_{amb} = 25 \ ^\circ\text{C} \end{split}$	-	-350	-500	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	310	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -0.5 A; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-0.89	-1	V
		I_C = -1 A; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.93	-1.1	V
		$\begin{split} &I_{C}=\text{-2 A; }I_{B}=\text{-200 mA; pulsed;} \\ &t_{p}\leq300\ \mu\text{s; }\delta\leq0.02\text{; }T_{amb}=25\ ^{\circ}\text{C} \end{split}$	-	-1.14	-1.25	V
V _{BE}	base-emitter voltage	I_C = -0.5 A; V _{CE} = -2 V; pulsed; t _p ≤ 300 μs; δ _{factor} ≤ 0.02; T _{amb} = 25 °C	-	-0.77	-0.9	V
t _d	delay time	I_{C} = -1 A; I_{Bon} = -50 mA; I_{Boff} = 50 mA;	-	10	-	ns
t _r	rise time	T _{amb} = 25 °C	-	80	-	ns
on	turn-on time		-	90	-	ns
t _s	storage time			195	-	ns

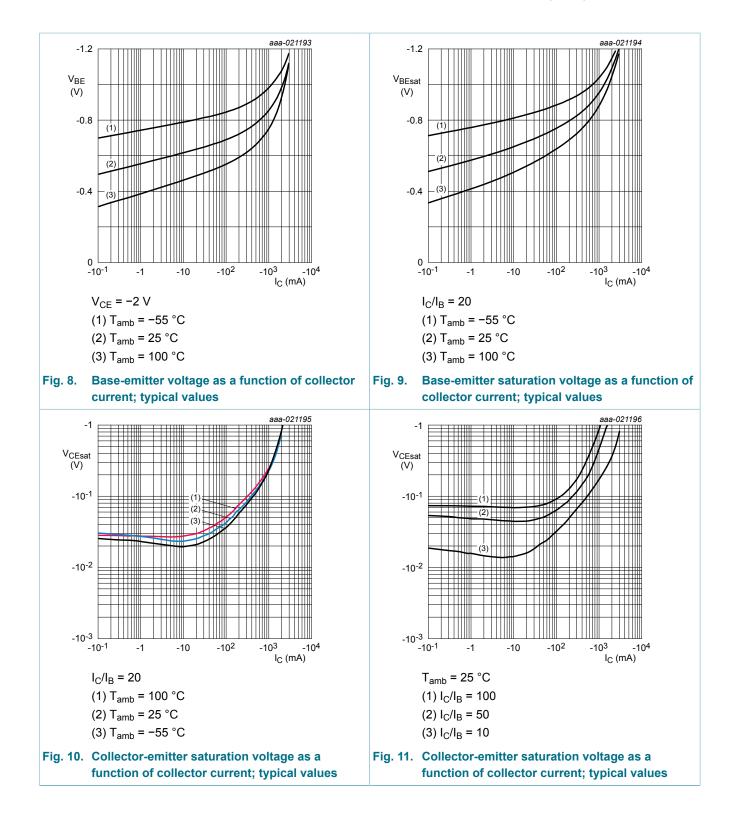
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t _f	fall time		-	75	-	ns
t _{off}	turn-off time		-	270	-	ns
f _T	transition frequency	V _{CE} = -10 V; I _C = -500 mA; f = 100 MHz; T _{amb} = 25 °C	-	100	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	16	-	pF



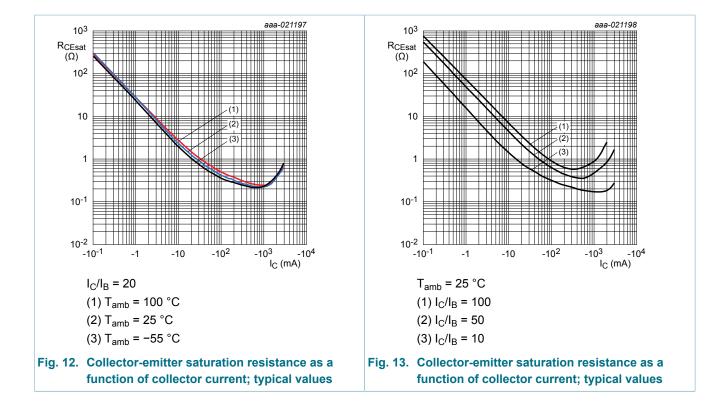
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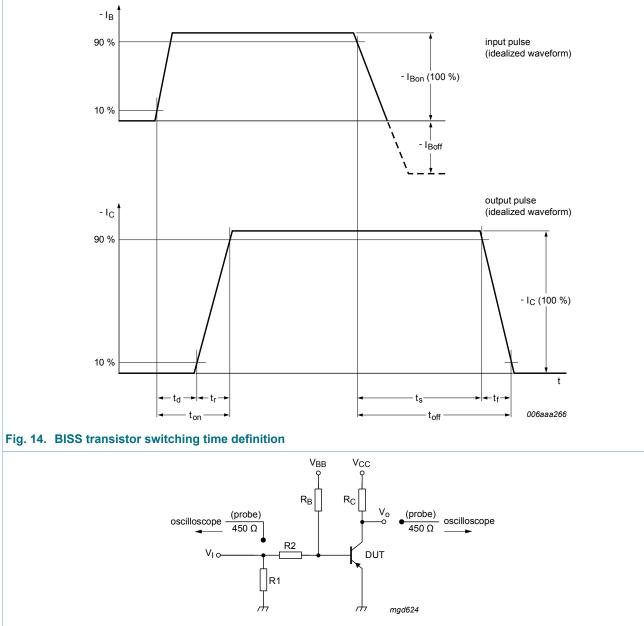


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11. Test information

Fig. 15. Test circuit for switching times

11.1 Quality information

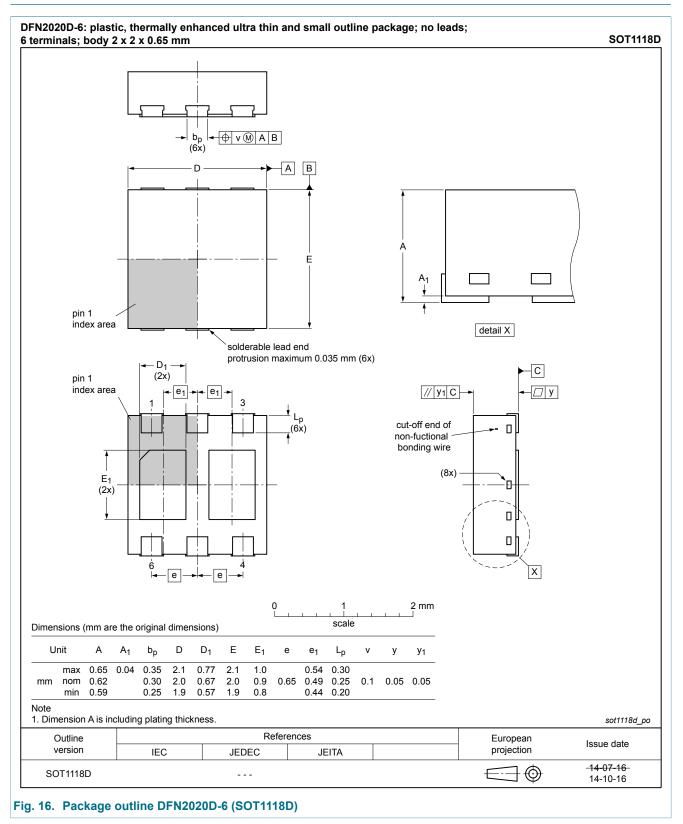
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12. Package outline



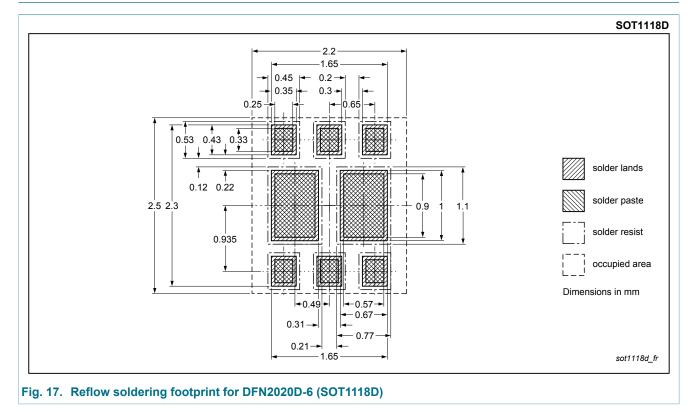
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13. Soldering



14. Revision history

Table 8. Revision his	able 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5260PAPS v.1	20151215	Product data sheet	-	-		

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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